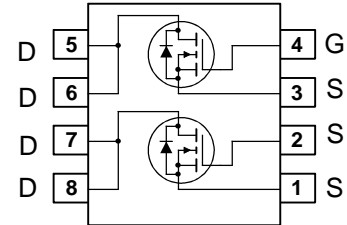


General Description

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- $V_{DS(V)} = 30V$
- $I_D = 6A (V_{GS} = 10V)$
- $R_{DS(ON)} < 28m\Omega (V_{GS}=10V)$
- $R_{DS(ON)} < 35 m\Omega (V_{GS}=4.5V)$
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability



Absolute Maximum Ratings $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1a)	6	A
	– Pulsed	20	
P_D	Power Dissipation for Single Operation (Note 1a)	1.6	W
	(Note 1b)	1.0	
	(Note 1c)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^{\circ}C$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	40	$^{\circ}C/W$

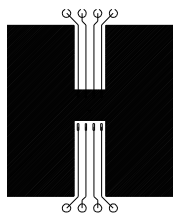
Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

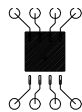
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		25		$\text{mV}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			1 10	μA
I_{GSS}	Gate–Source Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		-4.5		$\text{mV}/^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$		19 24	28 35	$\text{m}\Omega$
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	20			A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 6\text{ A}$		25		S
C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		575		pF
C_{oss}	Output Capacitance			145		pF
C_{rss}	Reverse Transfer Capacitance			65		pF
R_G	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		2.1		Ω
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		8	16	ns
t_r	Turn–On Rise Time			5	10	ns
$t_{d(off)}$	Turn–Off Delay Time			23	37	ns
t_f	Turn–Off Fall Time			3	6	ns
Q_g	Total Gate Charge		$V_{DS} = 15\text{ V}, I_D = 6\text{ A},$ $V_{GS} = 5\text{ V}$		5.8	8.1
Q_{gs}	Gate–Source Charge			1.7		nC
Q_{gd}	Gate–Drain Charge			2.1		nC
I_S	Maximum Continuous Drain–Source Diode Forward Current				1.3	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.3\text{ A}$ (Note 2)		0.75	1.2	V
t_{rr}	Diode Reverse Recovery Time	$I_F = 6\text{ A}, d_{IF}/d_t = 100\text{ A}/\mu\text{s}$		20		nS
Q_{rr}	Diode Reverse Recovery Charge				10	

Notes:

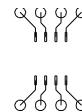
- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $78^\circ\text{C}/\text{W}$ when mounted on a 0.5 in^2 pad of 2 oz copper



b) $125^\circ\text{C}/\text{W}$ when mounted on a 0.02 in^2 pad of 2 oz copper



c) $135^\circ\text{C}/\text{W}$ when mounted on a minimum mounting pad.

Scale 1 : 1 on letter size paper

Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

Typical Characteristics

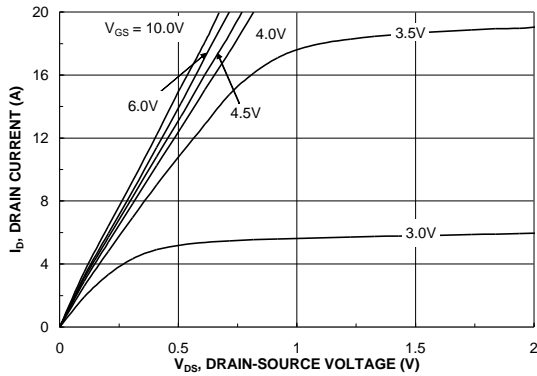


Figure 1. On-Region Characteristics.

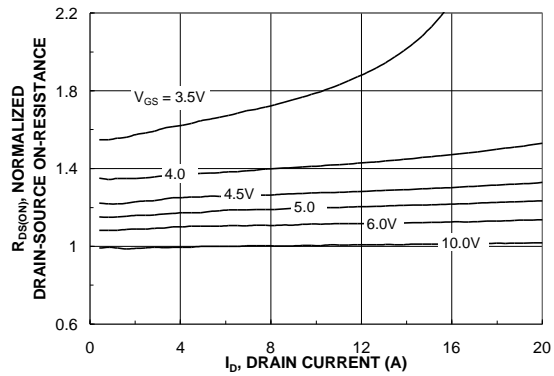


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

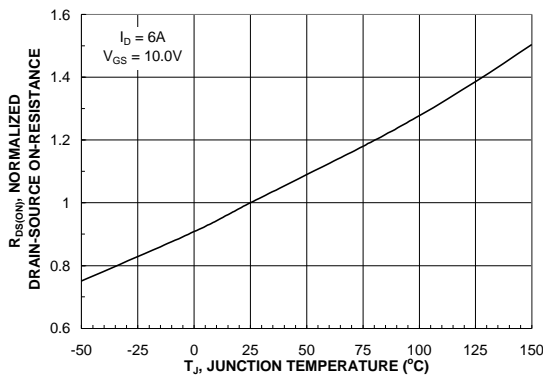


Figure 3. On-Resistance Variation with Temperature.

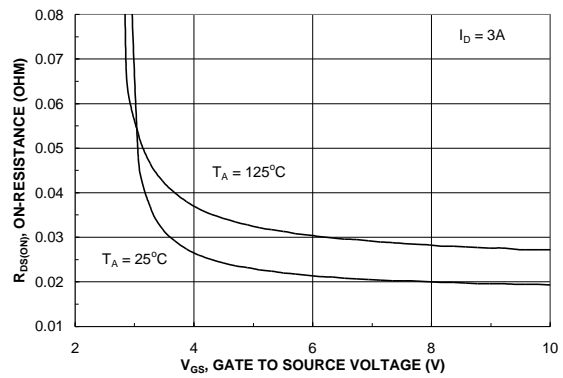


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

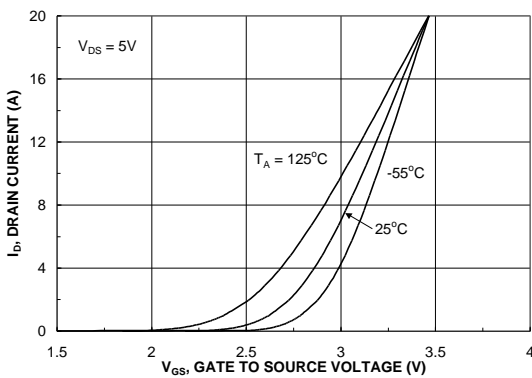


Figure 5. Transfer Characteristics.

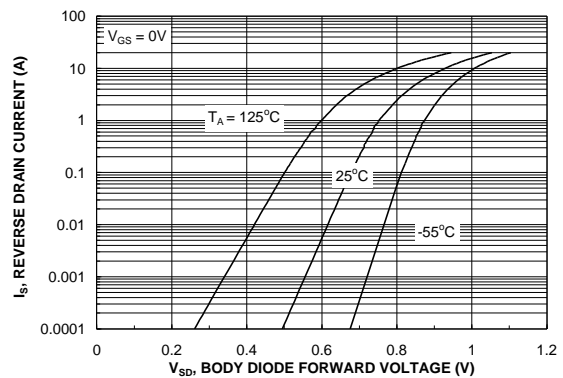


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

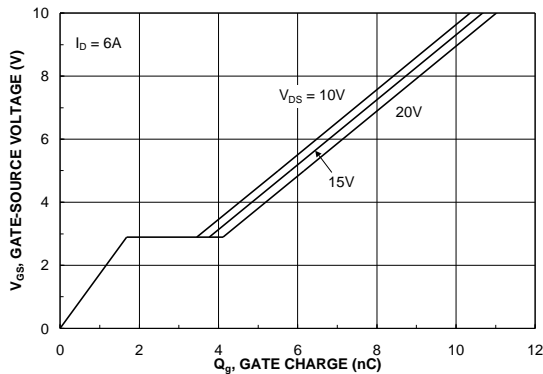


Figure 7. Gate Charge Characteristics.

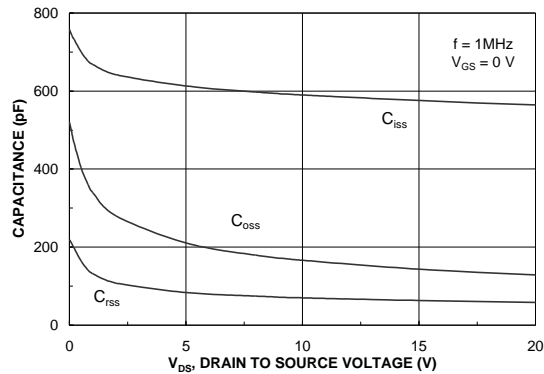


Figure 8. Capacitance Characteristics.

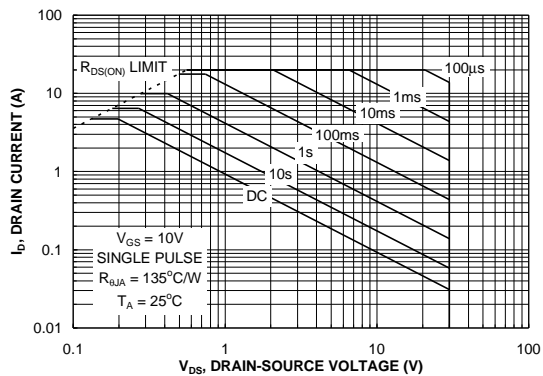


Figure 9. Maximum Safe Operating Area.

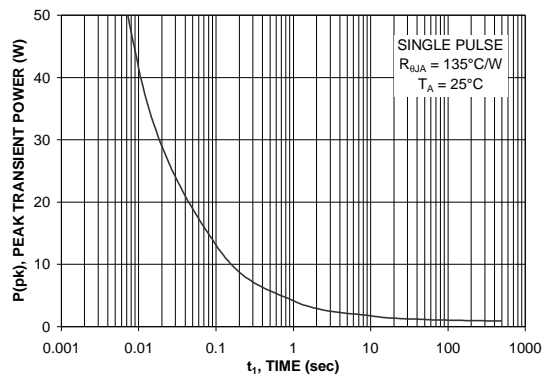


Figure 10. Single Pulse Maximum Power Dissipation.

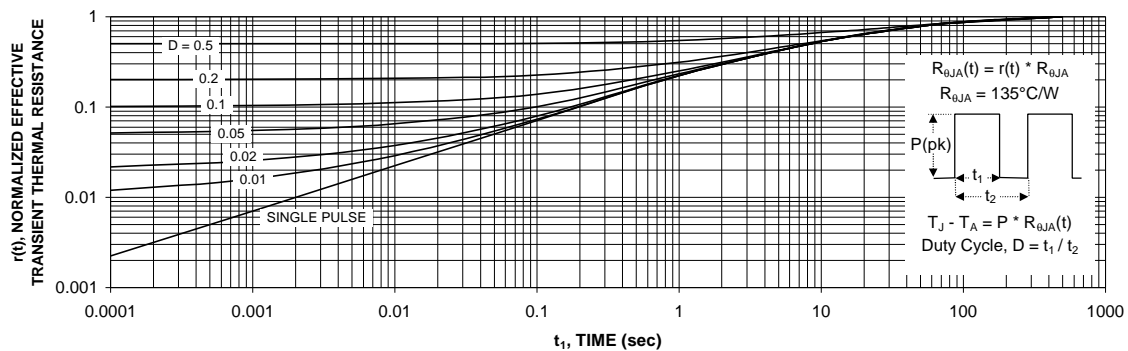
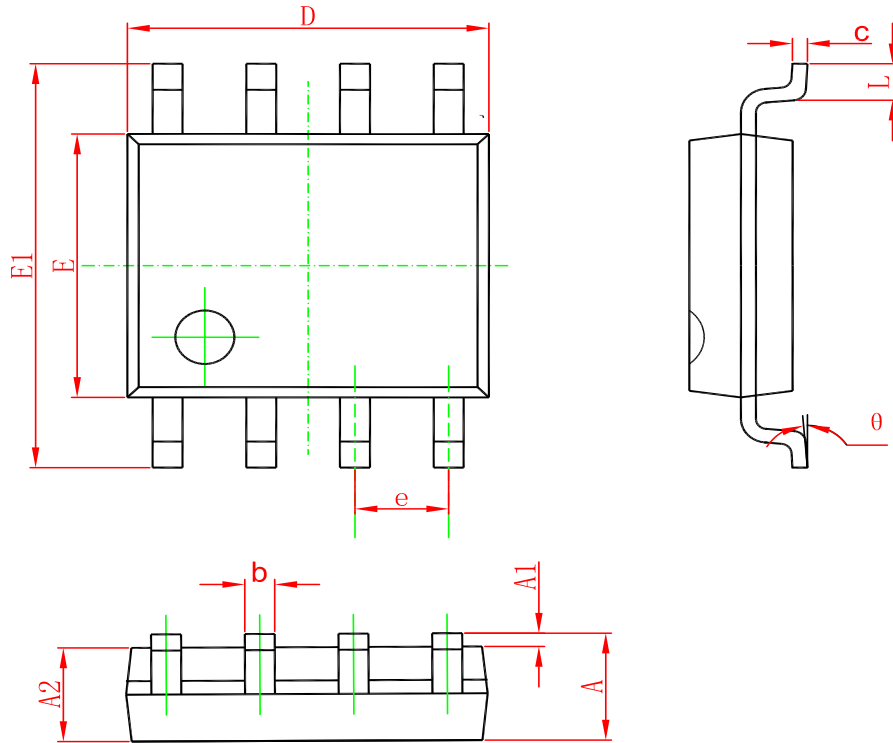


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

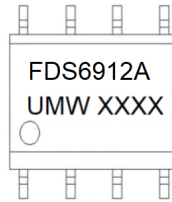
PACKAGE OUTLINE DIMENSIONS

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
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[DMN2990UFB-7B](#) [SSM3K35CT,L3F](#) [IPLK60R1K0PFD7ATMA1](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [IPWS65R035CFD7AXKSA1](#)
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